



N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^a	Q _g (Typ.)		
20	$0.85 \text{ at V}_{GS} = 4.5 \text{ V}$	0.4	0.335		
	1.08 at V _{GS} = 2.5 V	0.35	0.333		

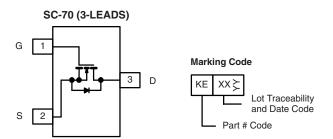
FEATURES Halogen-free According to IEC 61249-2-21 Definition

HALOGEN

FREE

TrenchFET® Power MOSFET 100 % R_g Tested

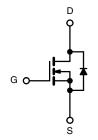
Compliant to RoHS Directive 2002/95/EC



Ordering Information: Si1300BDL-T1-E3 (Lead (Pb)-free)

Top View

Si1300BDL-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	S (T _A = 25 °C, unle	ess otherwise r	noted)	
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	20	V
Gate-Source Voltage		V _{GS}	± 8]
	T _C = 25 °C		0.4	
Continuous Proin Current (T. – 150 °C)	T _C = 70 °C	I _D	0.32	
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C		0.37 ^{b, c}	
	T _A = 70 °C		0.30 ^{b, c}	Α
Pulsed Drain Current		I _{DM}	0.5	
Continuous Source-Drain Diode Current	T _C = 25 °C	1	0.18	
Continuous Source-Diam Diode Current	T _A = 25 °C	l _S	0.14 ^{b, c}	
	T _C = 25 °C		0.2	
Maximum Power Dissipation	T _C = 70 °C]	0.14	w
	T _A = 25 °C	P _D	0.19] vv
	T _A = 70 °C		0.12 ^{b, c}	
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient ^{b, d}	t ≤ 5 s	R _{thJA}	540	670	°C/W		
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	450	570]		

Notes:

- a. Based on T_C = 25 °C.
- b. Surface mounted on 1" x 1" FR4 board.
- d. Maximum under steady state conditions is 360 °C/W.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	•		•	•			
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	J 050 A		20		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250 \mu A$		- 2.8			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.4		1.0	V	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V			± 100	nA	
Zana Oata Wallana Busin Oamani	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			100	nA	
Zero Gate Voltage Drain Current		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C			5	μΑ	
On-State Drain Current ^a		$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	0.4			Δ.	
	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 2.5 \text{ V}$	0.12			A	
Durin Course On Olate Berlineau	В	$V_{GS} = 4.5 \text{ V}, I_D = 0.25$		0.65	0.85		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 0.15$		0.85	1.08	Ω	
Dynamic ^b							
nput Capacitance	C _{iss}			35		pF	
Output Capacitance	C _{oss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		13			
Reverse Transfer Capacitance	C _{rss}			4			
Table Cata Observe	Qg	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 0.4$		560	840	pC	
Total Gate Charge				335	503		
Gate-Source Charge	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 2.5 \text{ V}, I_{D} = 0.35$		98			
Gate-Drain Charge	Q _{gd}			85			
Gate Resistance	R_{g}	f = 1 MHz	1.5	7	12	Ω	
Turn-On Delay Time	t _{d(on)}			7	12		
Rise Time	t _r	V_{DD} = 10 V, R_L = 25 Ω		10	15	- ns	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 0.4 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		8	13		
Fall Time	t _f			7	12		
Drain-Source Body Diode Characteristic	s						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			0.18	^	
Pulse Diode Forward Current ^a	I _{SM}				0.4	Α	
Body Diode Voltage	V_{SD}	I _S = 0.05 A		0.7	1.2	V	

Notes:

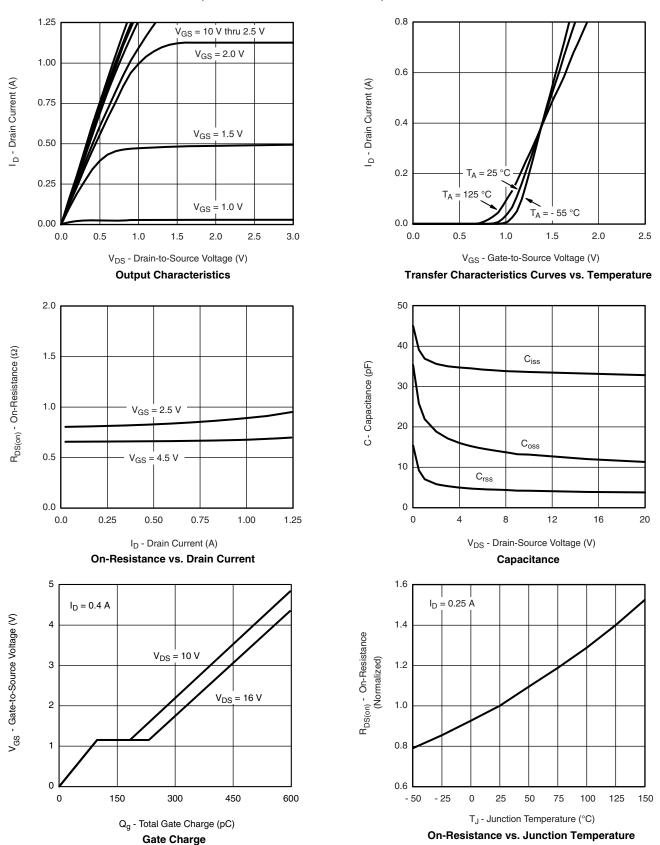
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

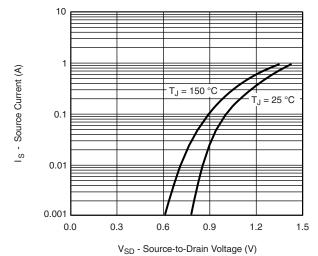


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

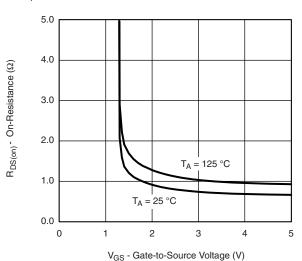


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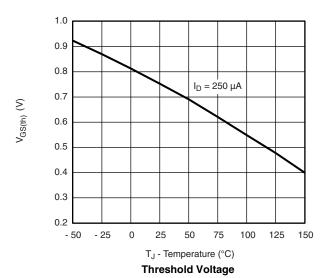
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Forward Diode Voltage vs. Temperature



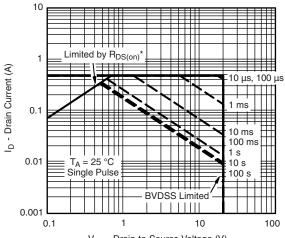
R_{DS(on)} vs. V_{GS} vs. Temperature



8 6 Power (W) 2 0 0.001 0.01 1000 Time (s)

10

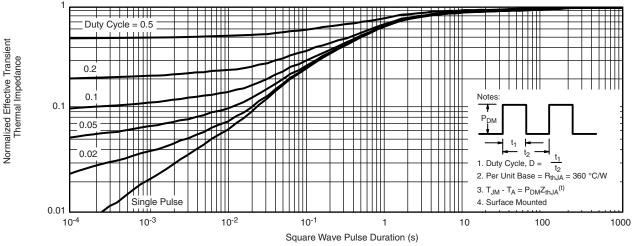
Single Pulse Power, Junction-to-Ambient



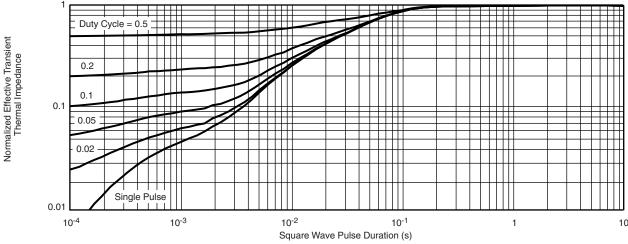
V_{DS} - Drain-to-Source Voltage (V) * V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified Safe Operating Area



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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Document Number: 73557 S11-2000-Rev. D, 10-Oct-11



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